

512MB – 64Mx72 SDRAM, UNBUFFERED, w/PLL

FEATURES

- PC100 and PC133
- Burst Mode Operation
- Auto and Self Refresh capability
- LVTTTL compatible inputs and outputs
- Serial Presence Detect with EEPROM
- Fully synchronous: All signals are registered on the positive edge of the system clock
- Programmable Burst Lengths: 1, 2, 4, 8 or Full Page
- Single Rank
- 3.3V ± 0.3V Power Supply
- 144 Pin SO-DIMM JEDEC
 - D1: 31.75 (1.25") TYP

DESCRIPTION

The WED3DG7266V is a 64Mx72 synchronous DRAM module which consists of nine 64Mx8 SDRAM components in TSOP II package, and one 2Kb EEPROM in an 8 pin TSOP package for Serial Presence Detect which are mounted on a 144 pin SO-DIMM multilayer FR4 Substrate.

NOTE: Consult factory for availability of:

- RoHS compliant products
- Vendor source control options
- Industrial temperature option

PIN CONFIGURATIONS (FRONT SIDE/BACK SIDE)

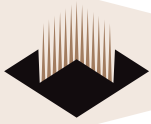
PINOUT											
PIN	FRONT	PIN	BACK	PIN	FRONT	PIN	BACK	PIN	FRONT	PIN	BACK
1	V _{ss}	2	V _{ss}	49	DQ13	50	DQ45	97	DQ22	98	DQ54
3	DQ0	4	DQ32	51	DQ14	52	DQ46	99	DQ23	100	DQ55
5	DQ1	6	DQ33	53	DQ15	54	DQ47	101	V _{cc}	102	V _{cc}
7	DQ2	8	DQ34	55	V _{ss}	56	V _{ss}	103	A6	104	A7
9	DQ3	10	DQ35	57	CB0	58	CB4	105	A8	106	BA0
11	V _{cc}	12	V _{cc}	59	CB1	60	CB5	107	V _{ss}	108	V _{ss}
13	DQ4	14	DQ36	61	CLK0	62	CKE0	109	A9	110	BA1
15	DQ5	16	DQ37	63	V _{cc}	64	V _{cc}	111	A10	112	A11
17	DQ6	18	DQ38	65	RAS#	66	CAS#	113	V _{cc}	114	V _{cc}
19	DQ7	20	DQ39	67	WE#	68	CKE1*	115	DQMB2	116	DQMB6
21	V _{ss}	22	V _{ss}	69	SO#	70	A12*	117	DQMB3	118	DQMB7
23	DQMB0	24	DQMB4	71	S1#*	72	NC	119	V _{ss}	120	V _{ss}
25	DQMB1	26	DQMB5	73	NC	74	CLK1	121	DQ24	122	DQ56
27	V _{cc}	28	V _{cc}	75	V _{ss}	76	V _{ss}	123	DQ25	124	DQ57
29	A0	30	A3	77	CB2	78	CB6	125	DQ26	126	DQ58
31	A1	32	A4	79	CB3	80	CB7	127	DQ27	128	DQ59
33	A2	34	A5	81	V _{cc}	82	V _{cc}	129	V _{cc}	130	V _{cc}
35	V _{ss}	36	V _{ss}	83	DQ16	84	DQ48	131	DQ28	132	DQ60
37	DQ8	38	DQ40	85	DQ17	86	DQ49	133	DQ29	134	DQ61
39	DQ9	40	DQ41	87	DQ18	88	DQ50	135	DQ30	136	DQ62
41	DQ10	42	DQ42	89	DQ19	90	DQ51	137	DQ31	138	DQ63
43	DQ11	44	DQ43	91	V _{ss}	92	V _{ss}	139	V _{ss}	140	V _{ss}
45	V _{cc}	46	V _{cc}	93	DQ20	94	DQ52	141	SDA	142	SCL
47	DQ12	48	DQ44	95	DQ21	96	DQ53	143	V _{cc}	144	V _{cc}

PIN NAMES

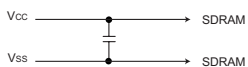
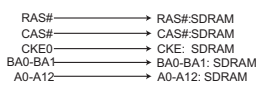
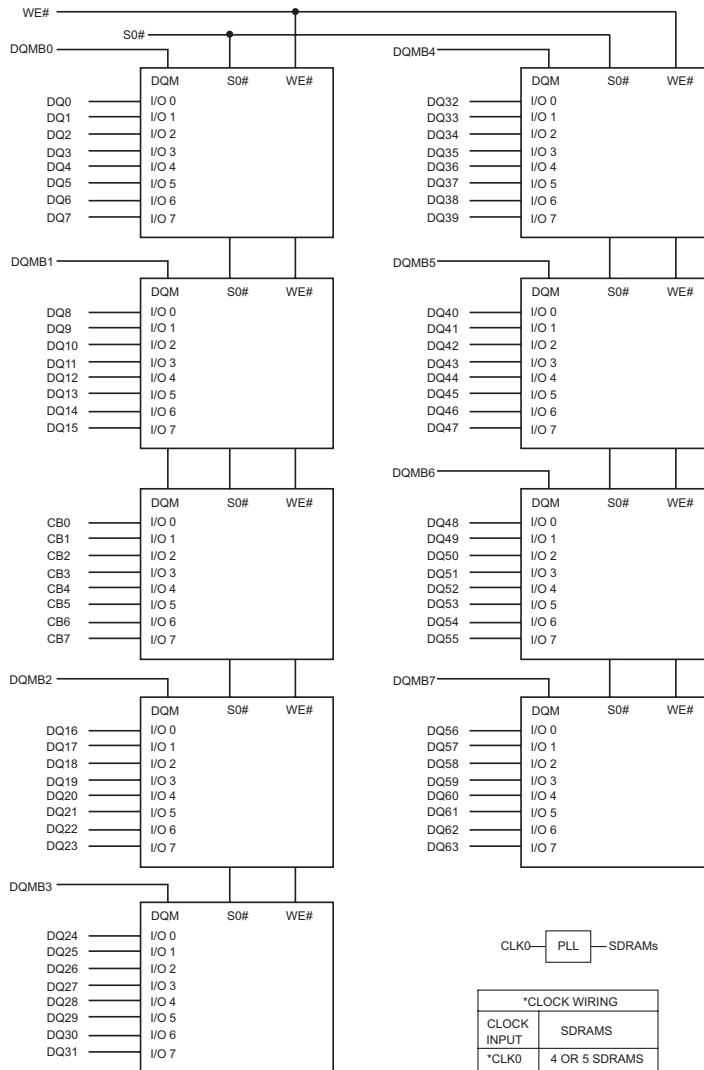
A0 – A12	Address Input (Multiplexed)
BA0-1	Select Bank
DQ0-63	Data Input/Output
CLK0, CLK1	Clock Input
CB0-7	Check Bit (Data-In/Data-Out)
CKE0	Clock Enable Input
CS0#	Chip Select Input
RAS#	Row Address Strobe
CAS#	Column Address Strobe
WE#	#Write Enable
DQM0-7	DQM
V _{cc}	Power Supply (3.3V)
V _{ss}	Ground
SDA	Serial Data I/O
SCL	Serial Clock
DNU	Do Not Use
NC	No Connect

* These pins are not used in this module

** These pins should be NC in the system which does not support SPD.

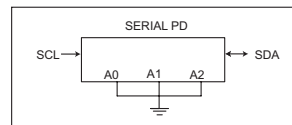


FUNCTIONAL BLOCK DIAGRAM



*CLOCK WIRING	
CLOCK INPUT	SDRAMS
*CLK0	4 OR 5 SDRAMs
*CLK1	4 OR 5 SDRAMs

NOTE: DQ wiring may differ than described in this drawing however, DQ/DQMB/CKE/S relationships must be maintained as shown.





ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Units
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on V _{CC} supply relative to V _{SS}	V _{CC} , V _{CCQ}	-1.0 ~ 4.6	V
Storage Temperature	T _{STG}	-55 ~ +150	°C
Power Dissipation	P _D	9	W
Short Circuit Current	I _{OS}	50	mA

Note: Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to recommended operating condition. Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

Voltage Referenced to: V_{SS} = 0V, 0°C ≤ T_A ≤ +70°C

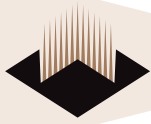
Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply Voltage	V _{CC}	3.0	3.3	3.6	V	
Input High Voltage	V _{IH}	2.0	3.0	V _{CCQ} + 0.3	V	1
Input Low Voltage	V _{IL}	-0.3	—	0.8	V	2
Output High Voltage	V _{OH}	2.4	—	—	V	I _{OH} = -2mA
Output Low Voltage	V _{OL}	—	—	0.4	V	I _{OL} = -2mA
Input Leakage Current	I _{LI}	-10	—	10	µA	3

Note: 1. V_{IH} (max) = 5.6V AC. The overshoot voltage duration is ≤ 3ns.
 2. V_{IL} (min) = -2.0V AC. The undershoot voltage duration is ≤ 3ns.
 3. Any input 0V ≤ V_{IN} ≤ V_{CCQ}
 Input leakage currents include Hi-Z output leakage for all bi-directional buffers with Tri-State outputs.

CAPACITANCE

T_A = 25°C, f = 1MHz, V_{CC} = 3.3V, V_{REF} = 1.4V ± 200mV

Parameter	Symbol	Max	Unit
Input Capacitance (A0-A12)	C _{IN1}	40	pF
Input Capacitance (RAS#,CAS#,WE#)	C _{IN2}	40	pF
Input Capacitance (CKE0)	C _{IN3}	40	pF
Input Capacitance (CK0)	C _{IN4}	6	pF
Input Capacitance (CS0#)	C _{IN5}	40	pF
Input Capacitance (DQM0-DQM7)	C _{IN6}	7	pF
Input Capacitance (BA0-BA1)	C _{IN7}	40	pF
Data Input/Output Capacitance (DQ0-DQ63)	C _{OUT}	9	pF
Data Input/Output Capacitance (CB0-7)	C _{OUT1}	9	pF



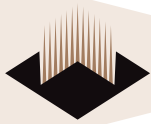
OPERATING CURRENT CHARACTERISTICS

(VCC = 3.3V, TA = 0°C ≤ +70°C)

Parameter	Symbol	Conditions	Version	Units	Note	
Operating Current (One bank active)	I _{CC1}	Burst Length = 1 t _{RC} ≥ t _{RC} (min) I _{OL} = 0mA	133/100	1,925	mA	1
Precharge Standby Current in Power Down Mode	I _{CC2P}	CKE ≤ V _{IL} (max), t _{CC} = 10ns	64	64	mA	
	I _{CC2PS}	CKE & CLK ≤ V _{IL} (max), t _{CC} = ∞	64			
Precharge Standby Current in Non-Power Down Mode	I _{CC2N}	CKE ≥ V _{IH} (min), CS ≥ V _{IH} (min), t _{CC} = 10ns Input signals are charged one time during 20	395	215	mA	
	I _{CC2NS}	CKE ≥ V _{IH} (min), CLK ≥ V _{IL} (max), t _{CC} = ∞ Input signals are stable	215			
Active Standby Current in Power-Down Mode	I _{CC3P}	CKE ≥ V _{IL} (max), t _{CC} = 10ns	100	100	mA	
	I _{CC3PS}	CKE & CLK ≤ V _{IL} (max), t _{CC} = ∞	100			
Active Standby Current in Non-Power Down Mode	I _{CC3N}	CKE ≥ V _{IH} (min), CS ≥ V _{IH} (min), t _{CC} = 10ns Input signals are changed one time during 20ns	575	420	mA	
	I _{CC3NS}	CKE ≤ V _{IH} (min), CLK ≤ V _{IL} (max), t _{CC} = ∞ Input signals are stable	420			
Operating Current (Burst mode)	I _{CC4}	I _O = mA Page burst 4 Banks activated t _{CCD} = 2CLK	133/100	1,925	mA	1
Refresh Current	I _{CC5}	t _{RC} ≥ t _{RC} (min)	133/100	3,095	mA	2
Self Refresh Current	I _{CC6}	CKE ≤ 0.2V	133/100	180	mA	

Notes:

1. Measured with outputs open.
2. Refresh period is 64ms.



ORDERING INFORMATION FOR D1

Ordering Information	Speed	CAS Latency	Height
WED3DG7266V10D1xx	100MHz	CL=2	31.75 (1.250") TYP
WED3DG7266V7D1xx	133MHz	CL=2	31.75 (1.250") TYP
WED3DG7266V75D1xx	133MHz	CL=3	31.75 (1.250") TYP

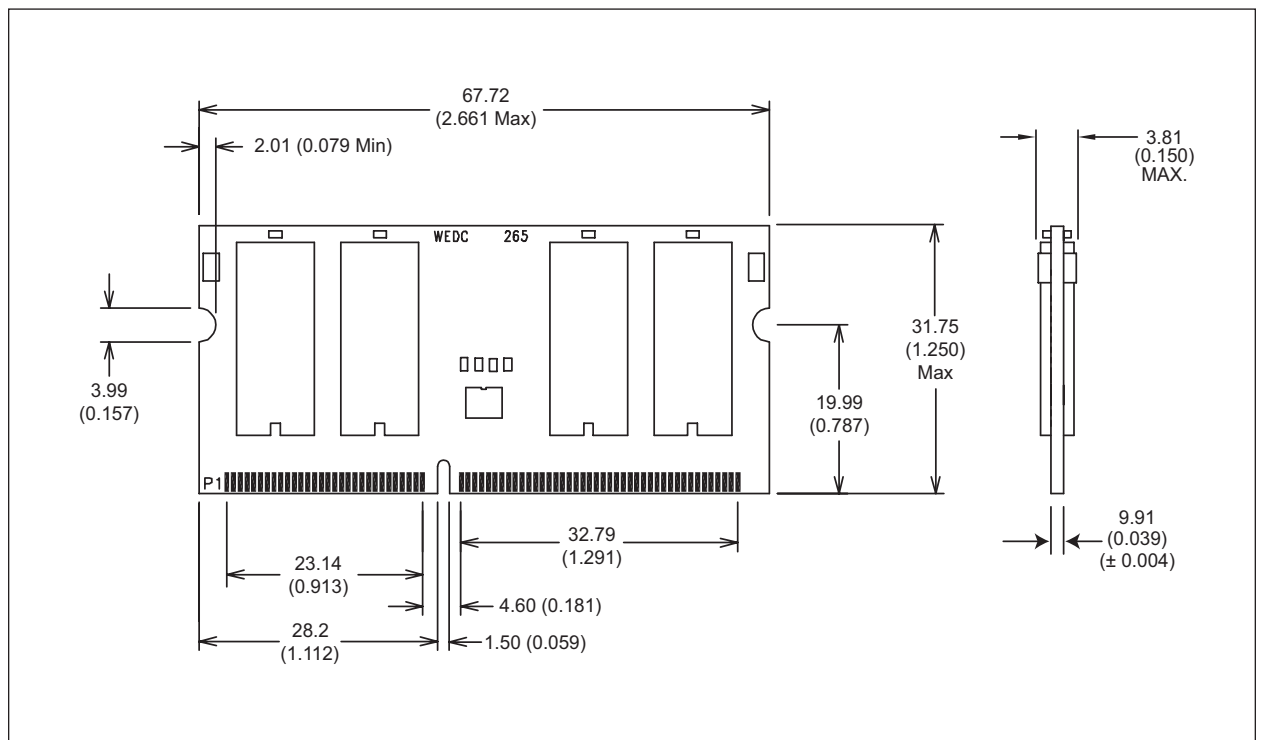
Industrial Temperature

Ordering Information	Speed	CAS Latency	Height
WED3DG7266V10D1I-xx	100MHz	CL=2	31.75 (1.250") TYP
WED3DG7266V7D1I-xx	133MHz	CL=2	31.75 (1.250") TYP
WED3DG7266V75D1I-xx	133MHz	CL=3	31.75 (1.250") TYP

Notes:

- Consult Factory for availability of RoHS products. (G = RoHS Compliant)
- Vendor specific part numbers are used to provide memory components source control. The place holder for this is shown as lower case "x" in the part numbers above and is to be replaced with the respective vendors code. Consult factory for qualified sourcing options. (M = Micron, S = Samsung & consult factory for others)
- Consult factory for availability of industrial temperature (-40°C to 85°C) option

PACKAGE DIMENSIONS FOR D1

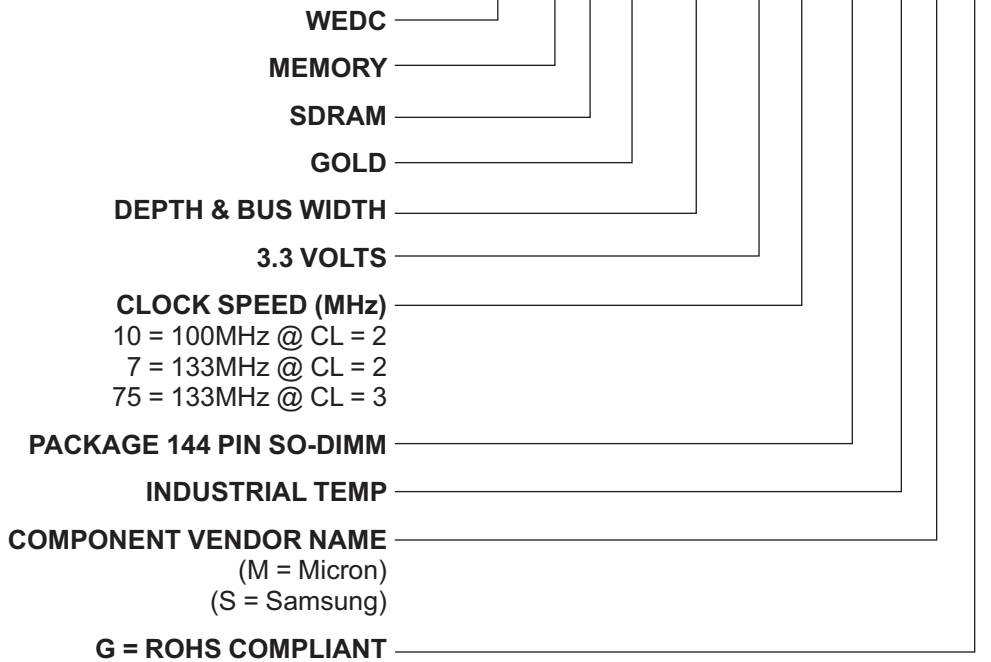


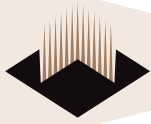
* ALL DIMENSIONS ARE IN MILLIMETERS AND (INCHES).



PART NUMBERING GUIDE

WED 3 D G 7266 V xx D1 I- x G



**Document Title**

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Revision History

Rev #	History	Release Date	Status
Rev A	Created	3-02	Advanced
Rev 0	0.1 Added PLL spec	6-04	Preliminary
	0.2 Updated CAP and IDD specs		
	0.3 Moved status from advanced to preliminary		
	0.4 Removed "ED" from part number		
	0.5 Moved from Advanced to preliminary		
Rev 1	1.1 Added "ED" to part number	7-05	Preliminary
Rev 2	2.1 Added RoHS, vendor source and industrial option notes	2-06	Preliminary
	2.2 Added part number guide		